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HISPEC[®] HI5000

Downhole Pressure Transducer

- Compact design
- NACE certified materials
- Silicon on sapphire sensor technology for outstanding stability
- High temperature up to 392 °F (200 °C)
- High pressure up to 29,000 psi (2,000 bar)
- All-welded and sealed construction for use in harsh and corrosive environments



The advanced sensor design consists of a piezoresistive silicon strain gauge circuit, which is epitaxially grown onto the surface of a sapphire diaphragm to form a single crystalline structure. The sapphire sensor element is then molecularly bonded to a titanium alloy sub-diaphragm.

This enables the sensor to endure higher over-pressures and provides superb corrosion resistance. The sensor exhibits virtually no hysteresis and excellent long-term stability over wide temperature ranges.

